

Semiconductor Device Modelling and Simulation
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Lecture – 39
Problem Session - 6

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PROBLEM-I

Use the equation

$$m \frac{dv}{dt} + \frac{mv}{\tau} = -eE$$

for the electron drift velocity to show that the conductivity at frequency ω is

$$\sigma(\omega) = \sigma(0) \frac{1 + i\omega\tau}{1 + (\omega\tau)^2}$$

Handwritten derivations on the slide include:

- $E = E_0 e^{-j\omega t}$
- $V = V_0 e^{-j\omega t}$
- $mV_0(-j\omega) e^{-j\omega t} + \frac{mV_0}{\tau} e^{-j\omega t} = -eE_0 e^{-j\omega t}$
- $V_0 = \frac{-eE_0}{m(-j\omega + \frac{1}{\tau})}$
- $V_0 = \frac{-eE_0}{m(1 - j\omega\tau)}$
- $\mu = \frac{-e\tau}{m(1 - j\omega\tau)}$
- $\sigma = ne\mu = \frac{-ne^2\tau}{m(1 - j\omega\tau)}$
- $\sigma(\omega) = \sigma(0) \frac{1 + i\omega\tau}{1 + (\omega\tau)^2}$
- $\sigma(0) = \frac{ne^2\tau}{m}$
- $\sigma = \frac{ne^2\tau}{m} \frac{1 + i\omega\tau}{1 + (\omega\tau)^2}$

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Hello, welcome to lecture number 39. So, we will take up some problems today. Use this equation governing the drift velocity of electron to show that the conductivity at frequency ω is given by the following expression. Here, it is basically a force balance equation where this is the force due to electric field then this is $m dv$ by dt which is mass into acceleration, so which is $f = ma$.

Then there is another force here which is called random force function. So, this is basically a force balance equation. Now, we have to calculate the drift velocity at frequency ω . So, let us assume that we are applying electric field $E = E_0 e^{-j\omega t}$ to the power $-j\omega t$. And let us say that the drift velocity follows the same expression. So, V is also $V_0 e^{-j\omega t}$ to the power $-j\omega t$. Now, let us substitute this equation number 1.

So, it becomes $m \frac{dv}{dt}$ becomes $mV_0(-j\omega) e^{-j\omega t} + \frac{mV_0}{\tau} e^{-j\omega t} = -eE_0 e^{-j\omega t}$. The $e^{-j\omega t}$ is common, so, it will cancel out. Then we can write $V_0 = \frac{-eE_0}{m(-j\omega + \frac{1}{\tau})}$.

divided by $-E$ naught divided by m times $-j\omega + m\tau$. So, this we can further write.

We can multiply and divide by τ , so, $-e\tau$ times E naught by m into $1 - j\omega\tau$. Now, we know that $V = \mu$ times E . So, from here we can find out the mobility $\mu = -e\tau$ by m into $1 - j\omega\tau$. And this mobility is related to the conductivity in semiconductor. That $\sigma = ne\mu$. So, it becomes $-ne^2\tau$ by m times $1 - j\omega\tau$. Now, σ naught, we can define, is σ at $\omega = 0$.

This is σ at $\omega = 0$, so that is $-ne^2\tau$ by m . So, from this we can write σ as σ naught times 1 over $1 - j\omega\tau$. Then we multiply it by $1 + j\omega\tau$ by $1 + j\omega\tau$ to get the expression. So, this is σ naught times $1 + j\omega\tau$ divided by $1 + \omega\tau$ whole square. So, this basically tells you that the conductivity is a function of frequency.

Then you also notice here there is a real part of conductivity and there is imaginary part of conductivity. Now, real part of conductivity is basically a real part of σ is σ naught by $1 + \omega\tau$ whole square. That means that $\omega = 0$ σ is simply σ naught. And at high frequency this conducted is actually decreasing. Then you can note the imaginary part of σ , so that will be $j\omega\tau$ σ naught by $1 + \omega\tau$ square so, at 0 frequency or DC.

This is basically goes to 0 and at high frequency it actually goes to $j\sigma$ naught by $\omega\tau$. So, it high frequency also it actually goes to 0. So, in between it peaks up at some frequency, so, your imaginary conductivity will look something like this. So, this will be some frequency relatively peak and then real conductor actually is always goes down with the frequency. So, this is the real part. This is imaginary part.

The real frequency because $j = \sigma E$. So, it is in the same phase that j and d are in the same phase. For imaginary part, they will be 90 degree out of phase. So, this conductivity if we consider a more general case of this because now we have considered only the electric field. We can consider the effect of magnetic field also because that also exerts a force.

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PROBLEM-2

For the drift velocity theory, show that the static current density can be written in matrix form as

$$\begin{bmatrix} j_x \\ j_y \\ j_z \end{bmatrix} = \frac{\sigma_0}{1 + (\omega_c \tau)^2} \begin{bmatrix} 1 & -\omega_c \tau & 0 \\ \omega_c \tau & 1 & 0 \\ 0 & 0 & 1 + (\omega_c \tau)^2 \end{bmatrix} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix} = \begin{bmatrix} \sigma_{xx} & \sigma_{xy} & \sigma_{xz} \\ \sigma_{yx} & \sigma_{yy} & \sigma_{yz} \\ \sigma_{zx} & \sigma_{zy} & \sigma_{zz} \end{bmatrix} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix}$$

In the high magnetic field limit of $\omega_c \tau \gg 1$, show that $\sigma_{xx} = ne\tau/B = -\sigma_{yy}$. In this limit, $\sigma_{xz} = 0$. The quantity σ_{xx} is called the Hall conductivity.

Handwritten notes:
 $\vec{B} = B_0 \hat{z}$
 $\frac{m \vec{v}}{\tau} + \frac{m \vec{v}}{\tau} = -e \vec{E} - e \vec{v} \times \vec{B}$
 $x \rightarrow \frac{m v_x}{\tau} = -e E_x - e v_y B_0 / c$
 $y \rightarrow \frac{m v_y}{\tau} = -e E_y + e v_x B_0 / c$
 $z \rightarrow \frac{m v_z}{\tau} = -e E_z$
 $v_x + \frac{e B_0 \tau}{m} v_y = -\frac{e \tau}{m} E_x$
 $v_y - \frac{e B_0 \tau}{m} v_x = -\frac{e \tau}{m} E_y$

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So, for that we have another problem here. It says from the drift velocity theory so that the static current density can be written in the matrix form as this. Now, if you look here, $j = \sigma E$. And this can be written as σ_{xx} , σ_{xy} , σ_{xz} , σ_{yx} , σ_{yy} , σ_{yz} , σ_{zx} , σ_{zy} , σ_{zz} times E_x , E_y , E_z . So now, it means that electric field is in x direction. If electric field is in x direction it can give component in the current component in x direction and y direction and z direction.

So, let us write here in terms of E_x $J_x = \sigma_{xx} E_x$. J_y is equal to that is a second here. So, σ_{yx} times E_x and J_z will be σ_{zx} times E_x . So, just E_x is able to give the current density in all the three directions. Now, how is it possible? Because that is a general case and it happens when there are certain constraints. So, let us write the same equation again $m \frac{dv}{dt} = -e E - e \vec{v} \times \vec{B}$.

Now, let us consider there is not only force due to electric field. Let us say there is a magnetic field also. So, we can write minus e times E is a vector minus e times $\vec{v} \times \vec{B}$. So, this will be more general case when both the electric field and magnetic field are present. Now, in this problem magnetic field is in z direction. So, let us say, \vec{B} vector is some B_0 in z direction and we have to find this relationship.

It is also shown here that static current density, so that means it is in a static situation. That means time derivative are 0 so, this will be 0 here. So, we will have $m \tau \frac{dv}{dt} = -e E - e \vec{v} \times \vec{B}$ and let us say, \vec{B} is in z direction. So, let us write for individual components

So which component of \mathbf{B} will give force in x direction. So, let us say this is x, y, z and \mathbf{B} is in this direction \mathbf{B} z direction. So, we have to get the force in y so, the velocity has to be in y direction. So, let us say, \mathbf{v} is in y direction cross \mathbf{B} in z direction. So, y cross z will give a component in x direction. So, it will be V by times B . Similarly, for y axis, we can write $m\mathbf{v}$ by $\tau = -e$ times $E_y - e$ times.

Now, for y your V has to be x in x direction, so, $V \times \hat{z}$, cross $B \hat{z}$, will give. Now, note the direction x cross z will give $-y$ cap. So, we have to write minus here so, minus, minus will become plus. So, it will be minus V_x times B similarly, for z cap mv_z by τ will be minus e times E_z . And for z direction the force due to B will not exist. Because when we take V cross B it will always be perpendicular to the B .

So because B is in z direction, so, it will not exert any force in this direction. So, with these three equations we can find out sigma xx, sigma xy, sigma yz. So, let us take first equation due to this x here, let us say this is the first equation. So, here, $V_x m \frac{dy}{dt} + e B y \frac{dx}{dt}$ is equal to minus e times E x. So, we can write $V_x + e B \frac{y}{m} \frac{dx}{dt} = -e \frac{dx}{dt} \frac{E_x}{m}$. So, this is basically the right side. So now, we can write this thing for all the three cases.

PROBLEM-2

For the drift velocity theory, show that the static current density can be written in matrix form as

$$\begin{bmatrix} j_x \\ j_y \\ j_z \end{bmatrix} = \frac{\sigma_0}{1 + (\omega_c \tau)^2} \begin{bmatrix} 1 & -\omega_c \tau & 0 \\ \omega_c \tau & 1 & 0 \\ 0 & 0 & 1 + (\omega_c \tau)^2 \end{bmatrix} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix}$$

In the high magnetic field limit of $\omega_c \tau \gg 1$, show that $\sigma_{xx} = ne\sigma_0/B = -e\sigma_{xy}$. In this limit, $\sigma_{zz} = 0$. The quantity σ_{xx} is called the Hall conductivity.

$$\frac{m}{\tau} v_x + (eB/c) v_y = -eE_x \Rightarrow$$

$$\frac{m}{\tau} v_y - (eB/c) v_x = -eE_y \Rightarrow$$

$$\frac{m}{\tau} v_z = -eE_z \Rightarrow$$

$$\text{Det} = \begin{vmatrix} 1 + (\omega_c \tau)^2 & -\omega_c \tau \\ \omega_c \tau & 1 + (\omega_c \tau)^2 \end{vmatrix} = 1 + (\omega_c \tau)^2$$

$$\begin{bmatrix} j_x \\ j_y \end{bmatrix} = \frac{-ne\sigma_0}{1 + (\omega_c \tau)^2} \begin{bmatrix} 1 & -\omega_c \tau \\ \omega_c \tau & 1 \end{bmatrix} \begin{bmatrix} E_x \\ E_y \end{bmatrix}$$

$$\begin{bmatrix} j_x \\ j_y \end{bmatrix} = \frac{-ne\sigma_0}{1 + (\omega_c \tau)^2} \begin{bmatrix} 1 & -\omega_c \tau \\ \omega_c \tau & 1 \end{bmatrix} \begin{bmatrix} E_x \\ E_y \end{bmatrix}$$

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So, we can write here V_x . One more thing here you can notice the force is $V \times B$. This is in q times $V \times B$. This is an SI unit but in this problem the unit they have chosen is Gaussian units. So, this force basically becomes q times $V \times B$ divided by C which is the velocity of light. So, this is nothing but a scaling factor relating the Gaussian unit to SI unit. So, this will appear here in this problem. So, it has to be $e V$ by C .

Now, $V_x + e B \tau$ by mc $V_y = -e \tau$ by m times E_x . Similarly, from this one $V_y - e B$ by $C \tau$ by m $V_x = -e \tau$ by m times E_y . And this is of course, simple $V_z = -e \tau$ by m times E_z . Now, we know that $j = -j = n$ times e times V . So, $J_x = ne V_x$. So, we can substitute here so, V_x can be written as J_x by ne . So, if you further substitute here so, what we get here? Let us write in matrix format is form itself.

So, let us say, J_x, J_y, J_z and V_x is J by ne . So, all the V_x can be replaced by J by ne or what we can do? We can multiply this thing by ne so, times ne times ne here. So, $ne V_x$ is J so, this becomes 1. Then it becomes $E ne^2 B \tau$ by mc . So, $ne^2 B \tau$ by mc . So, this becomes or we can just write $e B \tau$ by mc times J_y . So, this is J_y . So, it will now $e B \tau$ by mc plus this is $e B \tau$ by mc times J_y and there is no z component 0.

So, this is 0 and this is equal to this has to multiply by n so, $-ne^2 \tau$ by m . So, this is constant for all of them. So, you can write here E_x, E_y and E_z . Similarly, for second equation this is y is 1 so, y is in the middle line, so, this is one. For x you have minus $e B \tau$ by mc . There is no z component 0 and here x and y both are 0 z is 1. So, this also multiplied by ne so, ne is J_z so, this is 1.

So, a coefficient times J is equal to a constant times E_x, E_y, E_z . Now, what we have to do? We have to write this in terms of so, we have to take this matrix here. So, let us say this is something like A then $x \text{ vector} = B$ so, we can write. We multiply by A inverse to both sides. We get $x = x \text{ vector}$ is equal to A inverse times $B \text{ vector}$. So that is what we will get. So, let us rearrange it.

So, we can write J_x, J_y, J_z is equal to inverse of this matrix times $ne^2 \tau$ by m . So, if we take the inverse of this matrix, so, this we can keep as it is minus $ne^2 \tau$ by m times E_x, E_y, E_z and this is the inverse of this matrix here. That say this matrix is A . So, if you

take the inverse so, first, you have to take the determinant. So, inverse is basically the inverse has to be taken, as is a transpose of cofactor matrix divided by the determinant of the matrix.

So, the determinant of the matrix here will be 1. If we expand it then we can see actually for of diagonal element. It is always coming out to be 0. So, the determinant is 1 only. So, we do not have to divide by anything because the determinant is 1 only. So, determinant of this matrix is 1. So now, we have to take the cofactor matrix so, for the first element 1 into 1. So, this is 1 only so, we can write 1 here.

For this what is the term? So, this 1 will be $-e B \tau$ by mc . Now, this will come here because this is a transpose. So and this is basically with a inverted sign so, this will be $e B \tau$ by mc . So, you can write here $e B \tau$ by mc and the third one if you take so, this will be 0, so, this will be 0 here. Now, for this element will be minus $e B \tau$ by mc . So, this will be minus $e B \tau$ by mc . And for this element will be equal to 0.

Now, for the middle element, $1 - 0$ so, this will be 1 only. Then for this right side element, it will be 0, so, it will be 0. Then for this element it will be 0, so, this will also be 0. And then this for corner element this is $1 + e B \tau$ by mc whole square, so, this will be $1 + e B \tau$ by mc whole square. Now, this can be multiplied inside. So, if you notice here, this is $ne^2 \tau$ by m this be a value determined in the previous problem.

And this $e B$ by mc is cyclotron frequency, so, this term can be written as simply ω_C times τ ω_C is the cyclotron frequency times τ . So, we are exactly getting this matrix and this coefficient $ne^2 \tau$ is same as σ_0 by $1 + \omega_C^2 \tau^2$. So, we get this relationship relating the all the x, y, z component of the current density with the electric field.

So, when the magnetic field is present then the electric field in x direction can give the current in x direction current in y direction. May electric field in y direction can also give the current in x direction current in y direction. An electric field inject direction it can only give the electric field in z direction because the magnetic field is in z direction, so, there is no such force.

Now, at high magnetic field $\omega_C \tau$ will be much greater than one because this resonance frequency, the cyclotron frequency is basically eB/mc . So, at high field, this $\omega_C \tau$ will be quite large, so, $\omega_C \tau$ will be quite large. Then this is basically, if you compare, this is σ_{xx} , this is σ_{xy} and so on. So, this is σ_{yx} , σ_{yx} so, σ_{xy} $n \sigma_{yx}$ is $eB \tau/mc$ and this is $eB \tau/mc$.

And we have to multiply this thing by $ne^2 \tau$. So that is how you are getting it so, $eB \tau/mc$ times $ne^2 \tau$ by m . So, here we take this is a product but this σ_0 has to be taken out. σ_0 is $ne\mu$ which is n times e times $e \tau/m$. So, this has to be divided by σ_0 which is $ne^2 \tau/m$ and this is simply σ_0 . So, this is $eB \tau/mc$. So, we have $eB \tau/mc$. Then what you have done here?

We have divided and multiplied by this is $1 + \omega_C \tau$ square. So, this 1 here o I think we made a mistake here. Determinant is not 1. Determinant is $1 +$ this is 1. Let me create some space here determinant is $1 - eB \tau/mc$. So, this is the first column. The second column will be, it will be 0 and this will be 1. So, again $- eB \tau/mc$ so, it becomes $1 + eB \tau/mc$ whole square. The third column is 0.

So, determinant is this $1 + eB \tau/mc$ whole square, so, this is basically $1 + \omega_C \tau$ whole square. So, ω_C is eB/mc . So, this is divided by $1 + \omega_C \tau$ whole square. Then now, it is and this is of course σ_0 . Then a σ_{yx} is $\omega_C \tau$ times σ_0 y $1 + \omega_C \tau$ whole square, so, this is basically $\sigma_{yx} = \omega_C \tau$ times σ_0 $1 + \omega_C \tau$ whole square.

So, at high frequency 1 can be ignored, so, this will be σ_0 y $\omega_C \tau$. And $\omega_C \tau$ is $eB \tau/mc$. So, this is basically $eB \tau/mc$ in denominator and this is a numerator. So, if you find out e will cancel m will be cancel so, $e \tau$ will come cancel. So, you will simply have ne then $e \tau$ cancel by B and then C will go up. So, ne is C by B . So, this is what you are getting?

Now, the significance of this is that at high frequency in this limit, the conductivity σ_{xx} is 0. So, there is the conductivity to the electric field itself is going to 0 at high frequency. So, only the conductivity due to the magnetic field is, basically existing there. And this quantity

$\sigma_{\text{by } x}$ is called the whole conductivity. So, we could discuss two problems in this session. Thank you very much.